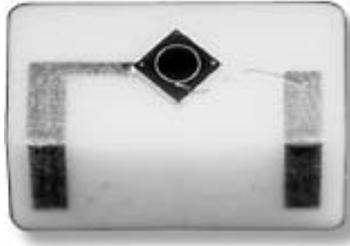


High Performance InGaAs p-i-n Photodiode

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13PD150-S

The 13PD150-S, an InGaAs photodiode with a 150 μ m-diameter photosensitive region and mounted on a metallized ceramic substrate, is intended for moderate-to-high speed applications. Efficiency coupling to multi-mode fiber in hybrid modules is enabled by the relatively large photosensitive area. Planar semiconductor design and dielectric passivation provide low noise performance. Reliability is assured by 100% purge burn-in (200°C, 15 hours, Vr = 20V). Chips can also be attached and wire bonded to customer-supplied or other specified packages.



Features:

- Planar Structure
- Dielectric Passivation
- 100% Purge Burn-in
- High Responsivity

DEVICE CHARACTERISTICS

Parameters	Test Conditions	Minimum	Typical	Maximum	Units
Operating Voltage				-20	Volts
Dark Current	-5V		0.5	2.5	nA
Capacitance	-5V		1.25	2	pF
Responsivity	1300nm	0.7	0.9		A/W
Rise/Fall				2	ns

ABSOLUTE MAXIMUM RATINGS

Reverse Voltage	20 Volts
Forward Current	5mA
Reverse Current	1mA
Operating Temperature	-40°C to +85°C
Storage Temperature	-40°C to +85°C
Soldering Temperature	250°C

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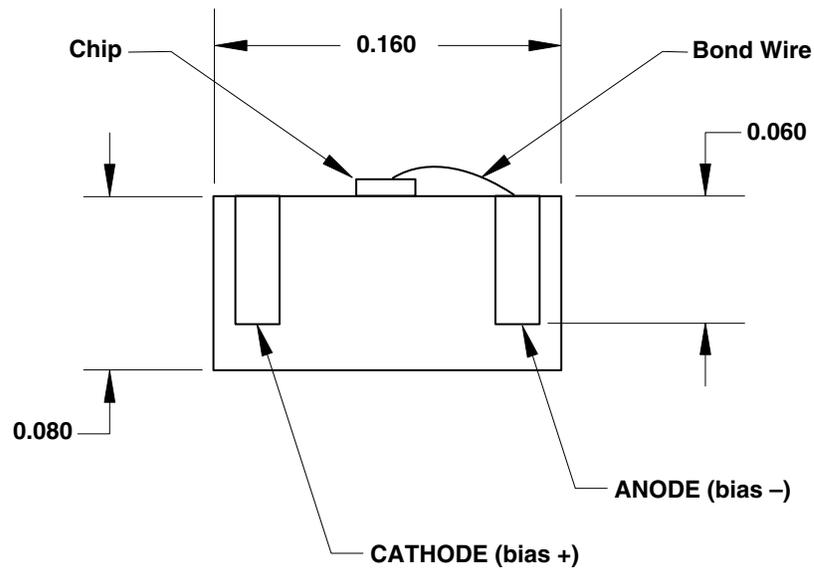
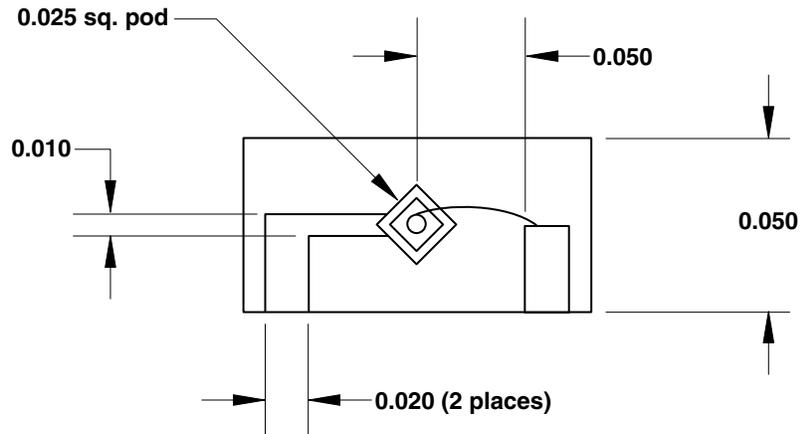
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Mechanical Specifications Ceramic Packages

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S1 Submount



Custom packaging is also available.

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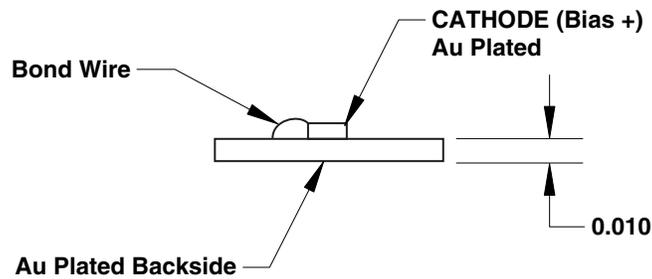
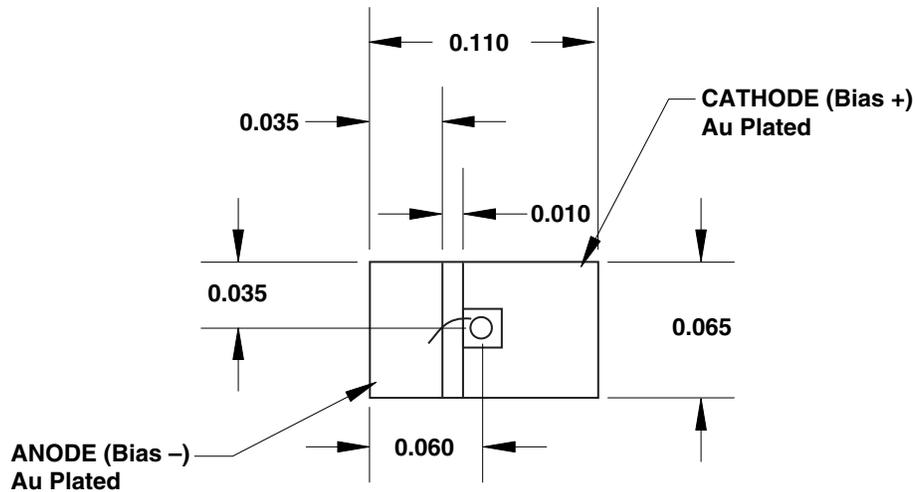


Mechanical Specifications

Ceramic Packages

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S2 Submount



Custom packaging is also available.

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